

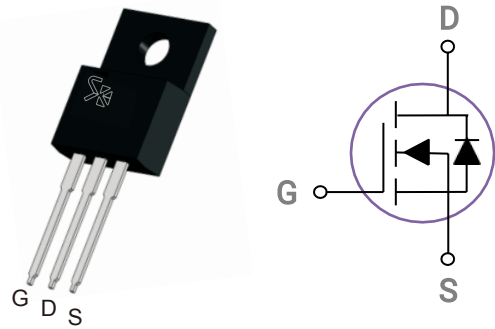
80V N Channel MOSFETs Datasheet

Features

- 80V, N-Channel, LowCiss
- $R_{DS(ON)}=5.9\text{m}\Omega(\text{Max.}) @V_{GS}=4.5\text{V } I_D=15\text{A}$
- $R_{DS(ON)}=4.8\text{m}\Omega(\text{Max.}) @V_{GS}=10\text{V } I_D=20\text{A}$

Applications

- Networking
- LED Lighting Applications
- Quick Charger Applications
- DC-DC Power Management



TO-220F

Absolute Maximum Ratings $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Unit
V_{DSS}	Drain-Source Voltage	80V	V
I_D	Continuous Drain Current	20A	A
V_{GSS}	Gate-Source Voltage	+20V / -12V	V
T_J	Operating Junction Temperature Range	-50 to 150°C	°C
T_{STG}	Storage Temperature Range	-50 to 150°C	°C

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}, I_D=250\mu\text{A}$	80	---	---	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=80\text{V}, V_{GS}=0\text{V}, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=64\text{V}, V_{GS}=0\text{V}, T_J=85^\circ\text{C}$	---	---	10	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=20\text{V}, V_{DS}=0\text{V}$	---	---	100	nA
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}, I_D=20\text{A}$	---	4.5	4.8	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}, I_D=15\text{A}$	---	5.6	5.9	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu\text{A}$	1	1.6	2.5	V

Note :

1. The data tested by pulsed, pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.

Electrical Characteristics ($T_J=25\text{ }^\circ\text{C}$, unless otherwise noted)

Dynamic Characteristics ^(Note1)

C_{iss}	Input Capacitance	$V_{DS}=25V, V_{GS}=0V,$ $F=1.0MHz$	-	1500	-	PF
C_{oss}	Output Capacitance		-	290	-	PF
C_{rss}	Reverse Transfer Capacitance		-	180	-	PF

Switching Characteristics ^(Note 1)

$t_{d(on)}$	Turn-on Delay Time	$V_{DD}=75V, R_L=5\Omega$ $V_{GS}=10V, R_{GEN}=3\Omega$	-	10.5	-	nS
t_r	Turn-on Rise Time		-	5.5	-	nS
$t_{d(off)}$	Turn-Off Delay Time		-	14.5	-	nS
t_f	Turn-Off Fall Time		-	3	-	nS
Q_g	Total Gate Charge	$V_{DS}=75V, I_D=10A,$ $V_{GS}=10V$	-	17	-	nC
Q_{gs}	Gate-Source Charge		-	4	-	nC
Q_{gd}	Gate-Drain Charge		-	4.4	-	nC

Drain-Source Diode Characteristics

V_{SD}	Diode Forward Voltage ^(Note 2)	$V_{GS}=0V, I_S=20A$	-	-	1.2	V
I_S	Diode Forward Current ^(Note 3)	-	-	-	20	A
t_{rr}	Reverse Recovery Time	$T_J = 25^\circ\text{C}, I_F = 10A$ $di/dt = 100A/\mu\text{s}$ ^(Note3)	-	32	-	nS
Q_{rr}	Reverse Recovery Charge		-	53	-	nC
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

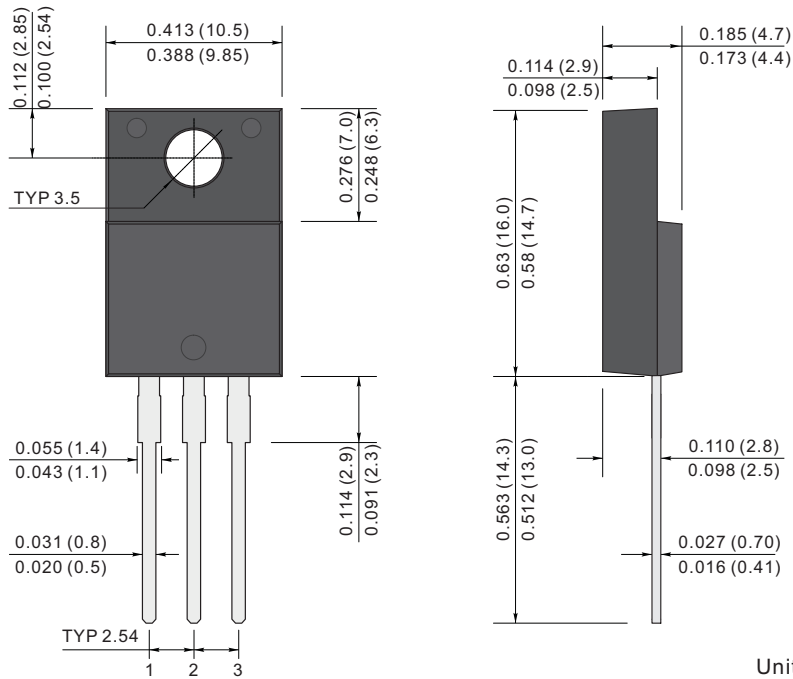
Notes:

1. Guaranteed by design, not subject to production
2. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.
3. Surface Mounted on FR4 Board, $t \leq 10$ sec.

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

TO-220F



单击下面可查看定价，库存，交付和生命周期等信息

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